



60V N-Channel Enhancement Mode MOSFET

Voltage

60 V

Current

20 A

Features

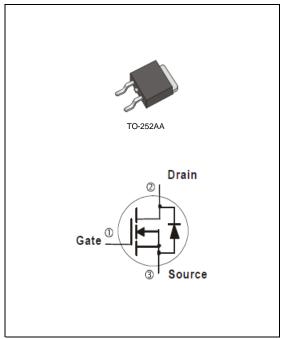
- $R_{DS(ON)}$, $V_{GS}@10V$, I_D $\overline{@10A<42m\Omega}$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@5A<52m\Omega$
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.. (Halogen Free)



• Case: TO-252AA Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0104 ounces, 0.297grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMET	ER	SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V	
Continuous Drain Current	T _C =25°C	I _D	20	A	
Continuous Drain Current	T _C =100°C		12		
Pulsed Drain Current (Note 1)	T _C =25°C	I _{DM}	80		
Davier Dissipation	T _C =25°C	Po	31	W	
Power Dissipation	T _C =100°C		12		
Ocationary Ducin Ocament	T _A =25°C	5	Α		
Continuous Drain Current	T _A =70°C	l _D	4	Α	
Power Dissipation	T _A =25°C		2.0	10/	
Power Dissipation	T _A =70°C	Po	1.3	W	
Single Pulse Avalanche Energy (Note 6)		E _{AS}	20	mJ	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C	
Typical Thermal Resistance	Junction to Case	$R_{ heta JC}$	4.0	°C/W	
(Note 4,5)	Junction to Ambient	$R_{\theta JA}$	62.5		

• Limited only By Maximum Junction Temperature





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	60	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250$ uA	1.0	1.8	2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =10A	-	36	42	mΩ	
		V _{GS} =4.5V,I _D =5A	-	40	52		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1.0	uA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 7)							
Total Gate Charge	Q_{g}		-	14	-	nC	
Gate-Source Charge	Qgs	V_{DS} =30V, I_{D} =10A, V_{GS} =10V (Note 1,2)	-	2.3	-		
Gate-Drain Charge	Q_{gd}		-	2.4	-		
Input Capacitance	Ciss	V_{DS} =25V, V_{GS} =0V, f =1.0MHZ	-	685	-	pF	
Output Capacitance	Coss		-	59	-		
Reverse Transfer Capacitance	Crss	I=1.UIVINZ	-	30	-		
Turn-On Delay Time	td _(on)	V_{DD} =15V, I_{D} =10A, V_{GS} =10V, R_{G} =6 Ω (Note 1,2)	-	4.5	-	ns	
Turn-On Rise Time	t _r		-	41	-		
Turn-Off Delay Time	td _(off)		-	19	-		
Turn-Off Fall Time	t _f		-	6	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	l.				20		
Diode Forward Current	I _S		-	-	20	A	
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	-	0.7	1.2	V	

NOTES:

- 1. Pulse width<a>300us, Duty cycle<a>2%
- 2. Essentially independent of operating temperature typical characteristics
- 3. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 4. The maximum current rating is package limited
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS} =20A, V_{DD} =25V, V_{GS} =10V
- 7. Guaranteed by design, not subject to production testing





TYPICAL CHARACTERISTIC CURVES

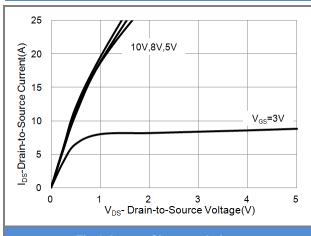
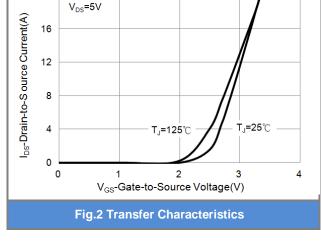


Fig.1 Output Characteristics



20

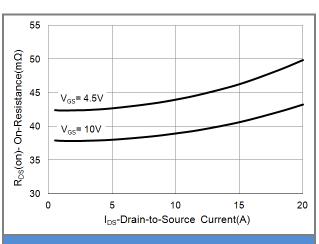


Fig.3 On-Resistance vs. Drain Current

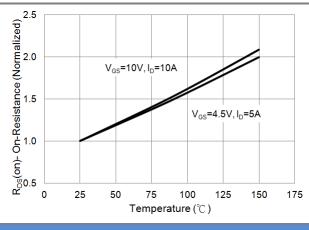
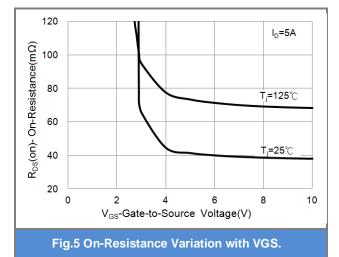


Fig.4 On-Resistance vs. Junction temperature



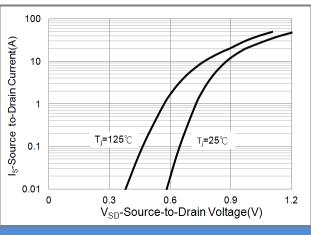


Fig.6 Source-Drain Diode Forward Voltage





TYPICAL CHARACTERISTIC CURVES

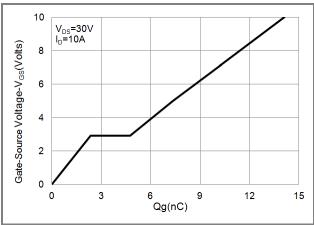
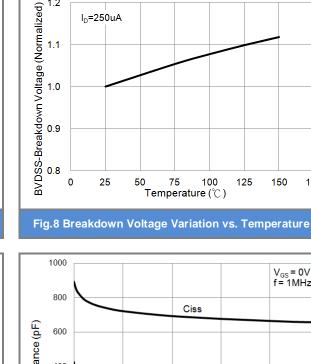


Fig.7 Gate-Charge Characteristics



I_D=250uA

1.1

1.0

100

125

175

150

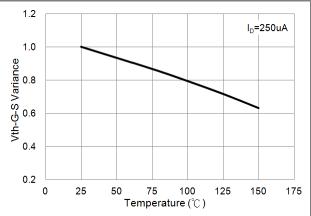


Fig.9 Threshold Voltage Variation with Temperature

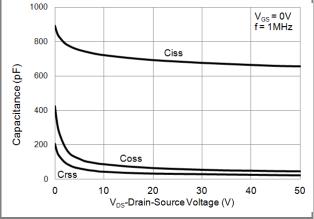
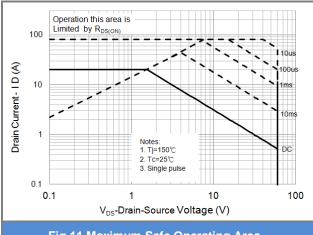


Fig.10 Capacitance vs. Drain-Source Voltage







TYPICAL CHARACTERISTIC CURVES

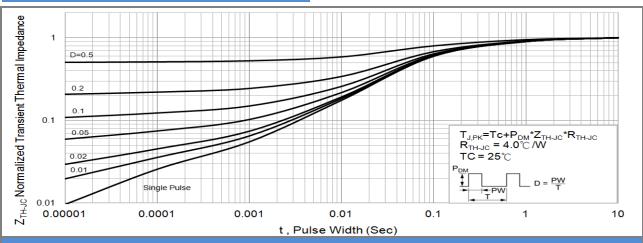
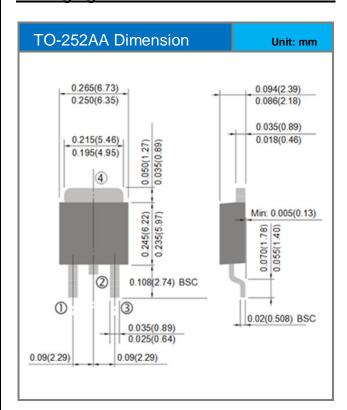


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width





Packaging Information



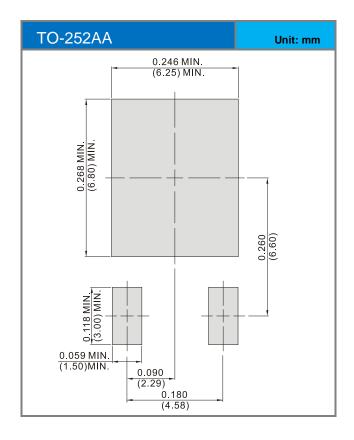




PART NO PACKING CODE VERSION

Part No Packing Code	Package Type Packing Ty		Marking	Version	
PJD20N06A_L2_00001	TO-252AA	3,000pcs / 13" reel	D20N06A	Halogen free	

MOUNTING PAD LAYOUT







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